

ABSTRACT

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Disclosed is an epitaxial growth furnace for effecting the formation of an epitaxial layer on the surface of a semiconductor wafer by CVD in a reaction chamber of the furnace. The furnace comprises a wafer holder having an opening for exposing an surface area of the wafer which surface area is subject to epitaxial growth, an opening flange adapted for engagement with a chamfered tapered face of a whole peripheral edge of the wafer on the side of said surface area thereof, and a plurality of jaw means adapted for detachably engaging with an outer periphery of the wafer on a back surface side of said surface area.

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